REMARKS

In response to the restriction requirement set forth in the Office Action mailed May 5, 2005, Applicant confirms election of Group I, claims 1-25. Such election is made without traverse.

Claims 1-6, 9-19 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nguyen (US 2004/0169281) in view of Sirringhauss (US 2004/0266207). Claims 7-8, 20-25 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nguyen in view of Sirringhauss as applied to claim 1 above, and further in view of Wakamoto (US 6,455,214). These rejections are respectfully traversed.

Nguyen discloses a method for forming conductive features wherein a layer of nanotubes is deposited by plasma enhanced CVD on a catalytic seed layer 102 on a substrate 100, and subsequent patterning of the nanotube layer by depositing a photoresist 108, patterning the photoresist 108 using conventional techniques, and etching the layer of nanotubes using the photoresist as a mask. Conductive material 110 is deposited in the opening [0020]. In such plasma CVD deposition process, the seed layer nucleates the growth of the layer of nanotubes. As noted by the Examiner, Nguyen does not disclose that the manufacturing process is continuously, with the substrate moving. Sirringhauss teaches that high throughput at low cost could be achieved in the manufacturing of polymer transistor circuits when a continuous sheet of flexible substrate is moved through a series of processing stations [0078]. The Examiner states that it would have been obvious to one of ordinary skill in the art to have the manufacturing process of Ngyuen be a continuous manufacturing process with a moving substrate because Sirringhauss teaches that high throughput at low cost is achieved when a continuous sheet of flexible substrate is moved through a series of processing stations.

With respect to the rejection of Claims 1-6, 9-19, as noted above, Ngyuen describes forming the nanotube layer thereof by a <u>plasma enhanced CVD</u> deposition process onto a seed catalytic layer. Such PECVD technique would in the first instance be difficult to use in a continuous process. While Sirringhauss may include generic references to advantages of continuous processes, there is no useful specification as to coating materials of the type deposited by PECVD in

Ngyuen. Further, even if the PECVD process of Ngyuen was modified to provide a continuous process with a moving substrate, the present claimed invention would in any event not be obtained as the present claimed invention is specifically directed towards forming a conductive layer by coating of a dispersion containing conductive nano-materials and drying of the coated dispersion wherein the nanoparticles self-align into a conductive layer. Thus, the combination of Nguyen and Sirringhauss clearly fails to establishing a prima facie case of obviousness with respect to the present claimed invention. Rather, the present claimed invention is uniquely designed to facilitate formation of patterned nano-material conductive layers in a continuous process, in a specific manner not taught or suggested by either of Ngyuen or Sirringhauss, either alone or in combination. Reconsideration of this rejection is accordingly respectfully requested.

With respect to the rejection of claims 7-8, 20-25, Wakamoto fails to overcome the deficiencies of the basic combination of Nguyen and Sirringhauss with respect to establishing a prima facie case of obviousness as discussed above, as it also fails to teach or suggest a nano-material dispersion continuous coating/drying/self-alignment and subsequent patterning steps of the present claimed process. Reconsideration of this rejection is accordingly also respectfully requested.

In view of the foregoing remarks, reconsideration of this patent application is respectfully requested. A prompt and favorable action by the Examiner is earnestly solicited. Should the Examiner believe any remaining issues may be resolved via a telephone interview, the Examiner is encouraged to contact Applicants' representative at the number below to discuss such issues.

Respectfully submitted,

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If the Examiner is unable to reach the Applicant(s) Attorney at the telephone number provided, the Examiner is requested to communicate with Eastman Kodak Company Patent Operations at (585) 477-4656.